

DUAL POWER OPERATIONAL AMPLIFIER

PRELIMINARY DATA

- OUTPUT CURRENT TO 1A
- OPERATES AT LOW VOLTAGES
- SINGLE OR SPLIT SUPPLY
- LARGE COMMON-MODE AND DIFFERENTIAL MODE RANGE
- GROUND COMPATIBLE INPUTS
- LOW SATURATION VOLTAGE
- THERMAL SHUTDOWN

The L272D is a monolithic integrated circuit in SO-16 packages intended for use as power operational amplifier in a wide range of applica-

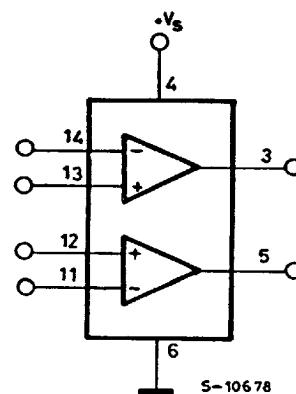
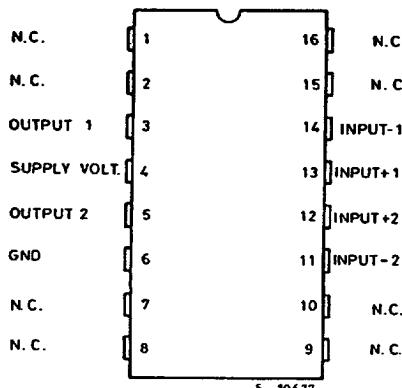
cations including servo amplifiers and power supplies, compact disc, VCR, etc. The high gain and high output power capability provide superior performance wheatever an operational amplifier/power booster combination is required.


SO-16J
ORDERING NUMBER: L272D

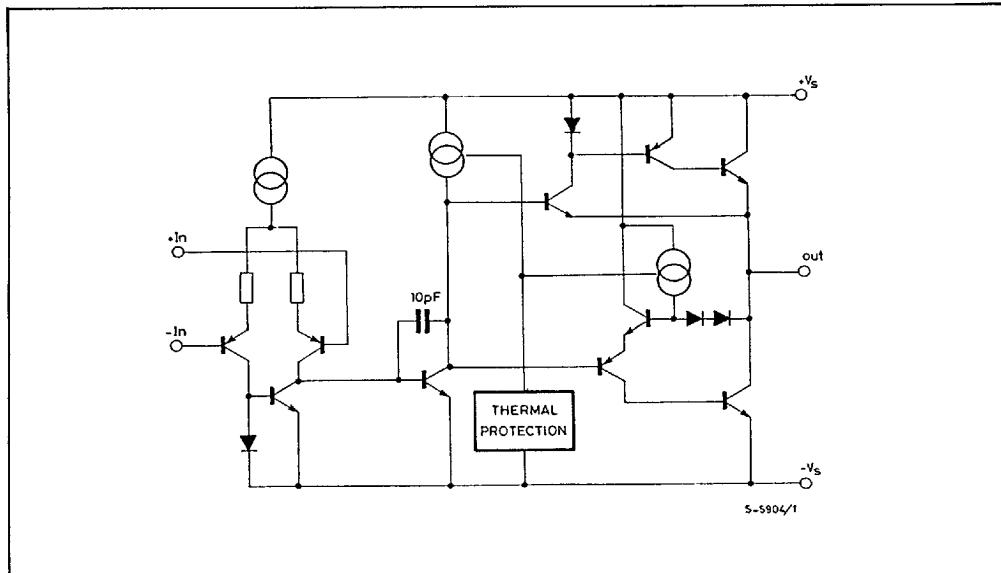
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_s	Supply voltage	28	V
V_i	Input voltage	V_s	
V_d	Differential input voltage	$\pm V_s$	
I_o	DC Output current	1	A
I_p	Peak output current (non repetitive)	1.5	A
P_{tot}	Power dissipation at $T_{case} = 90^\circ\text{C}$	1.2	W
T_{op}	Operating Temperature Range	-40 to +85	$^\circ\text{C}$
T_{stg}, T_j	Storage and junction temperature	-40 to 150	$^\circ\text{C}$

CONNECTION DIAGRAMS



SCHEMATIC DIAGRAM (one only)



THERMAL DATA

$R_{thj\text{-alumina}}(*)$	Thermal resistance junction-alumina	max 50	$^{\circ}\text{C/W}$
-----------------------------	-------------------------------------	--------	----------------------

(*) Thermal resistance junctions-pins with the chip soldered on the middle of an alumina supporting substrate measuring 15 x 20 mm; 0.65 mm thickness and infinite heatsink.

ELECTRICAL CHARACTERISTICS ($V_s = 24V$, $T_{amb} = 25^\circ C$ unless otherwise specified)

Parameter	Test Conditions		Min.	Typ.	Max.	Unit
V_s	Supply voltage		4		28	V
I_s	Quiescent drain current	$V_o = \frac{V_s}{2}$	$V_s = 24V$	8	12	mA
			$V_s = 12V$	7.5	11	mA
I_b	Input bias current			0.3	2.5	μA
V_{os}	Input offset voltage			15	60	mV
I_{os}	Input offset current			50	250	nA
SR	Slew rate			1		$V/\mu s$
B	Gain-bandwidth product			350		KHz
R_i	Input resistance		500			$K\Omega$
G_v	O.L. voltage gain	$f = 100Hz$	60	70		dB
		$f = 1KHz$		50		dB
e_N	Input noise voltage	$B = 20KHz$		10		μV
I_N	Input noise current	$B = 20KHz$		200		pA
CRR	Common Mode rejection	$f = 1KHz$	60	75		dB
SVR	Supply voltage rejection	$f = 100Hz$ $R_G = 10K\Omega$ $V_R = 0.5V$	$V_s = 24V$ $V_s = \pm 12V$ $V_s = \pm 6V$	54 62 56	70 62 56	dB dB dB
V_o	Output voltage swing		$I_p = 0.1A$ $I_p = 0.5A$	21	23 22.5	V V
C_s	Channel separation	$f = 1KHz; R_L = 10\Omega$	$G_v = 30dB$ $V_s = 24V$ $V_s = \pm 6V$		60 60	dB dB
d	Distortion	$f = 1KHz$ $V_s = 24V$	$G_v = 30dB$ $R_L = \infty$		0.5	%
T_{sd}	Thermal shutdown junction temperature				145	$^\circ C$

■ 7929237 0052655 445 ■

3/4

101

Fig. 1 - Quiescent current vs. supply voltage

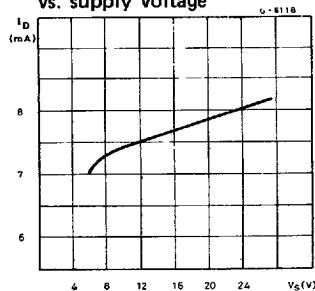


Fig. 2 - Quiescent drain current vs. temperature

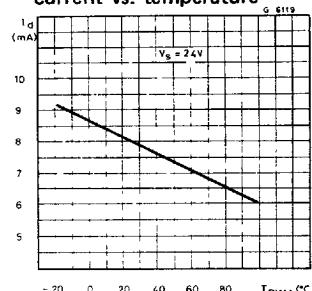


Fig. 3 - Open loop voltage gain

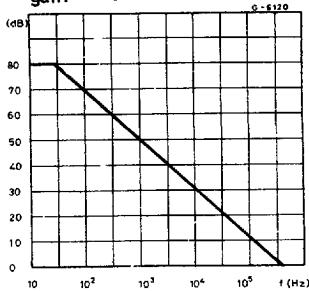


Fig. 4 - Output voltage swing vs. load current

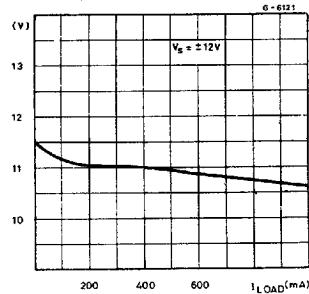


Fig. 5 - Output voltage swing vs. load current

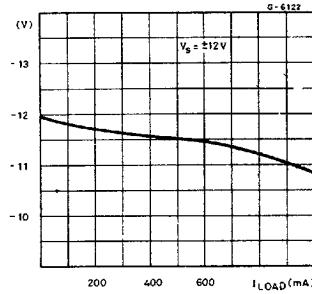


Fig. 6 - Supply voltage rejection vs. frequency

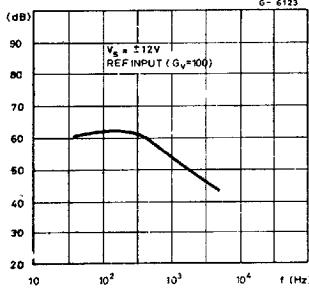


Fig. 7 - Channel separation vs. frequency

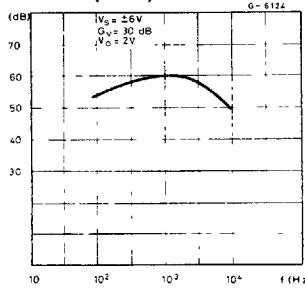


Fig. 8 - Common mode rejection vs. frequency

